SAMYANG ELECTRONICS *MBR820CT --- MBR8200CT*

SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE: 20 --- 200 V
CURRENT: 8.0A

FEATURES

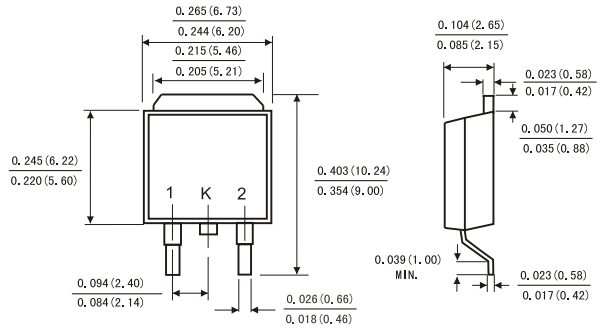
- ◇Metal-semiconductor junction with guard ring
- ◇Epitaxial construction
- ◇Low forward voltage drop,low switching losses
- ◇High surge capability
- ◇For use in low voltage,high frequency inverters free wheeling,and polarity protection applications
- ◇The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

- ◇Case:JEDEC TO-252, molded plastic
- ◇Terminals: Axial lead ,solderable per MIL- STD-750,Method 2026
- ◇Polarity: As marked
- ◇Weight: 0.08 ounces,0.24 grams
- ◇Mounting position: Any

TO - 252

(DPAK)



Dimensions in inches and (milimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase,half wave,60 Hz,resistive or inductive load. For capacitive load,derate by 20%.

	Symbols	MBR 820CT	MBR 830CT	MBR 840CT	MBR 850CT	MBR 860CT	MBR 880CT	MBR **8100CT**	MBR 8150CT	MBR 8200CT	Units
Maximum repetitive peak reverse voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	Volts
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	Volts
Maximum DC blocking voltage	V_{DC}	20	30	40	50	60	80	100	150	200	Volts
Maximum average forward rectified current(see Fig.1) Per leg	$I_{(AV)}$	4.0									Amps
Maximum average forward rectified current(see Fig.1) Total device	$I_{(AV)}$	8.0									Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I_{FSM}	150.0									Amps
Maximum instantaneous forward voltage at 8.0 A(Notes 1)	V_F	0.60			0.75		0.85		0.90	0.95	Volts
Maximum instantaneous reverse current at rated DC blocking voltage(Notes 1) T_A=25℃	I_R	0.2									mA
Maximum instantaneous reverse current at rated DC blocking voltage(Notes 1) T_A=125℃	I_R	15			50						mA
Typical thermal resistance (Notes 2)	$R_{\theta JC}$	2.5									℃/W
Operating junction temperature range	T_J	-65 to+150									℃
Storage temperature range	T_{STG}	-65 to+150									℃

NOTE: 1. Pulse test:300us pulse width,1% duty cycle.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
3.Thermal resistance junction to ambient

FIG.1-FORWARD CURRENT DERATING CURVE

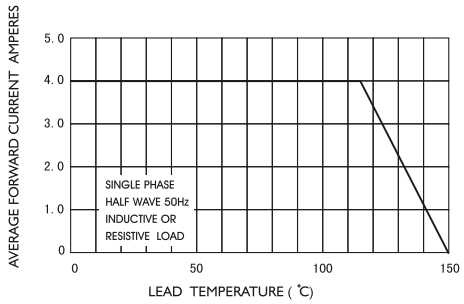


FIG.2-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

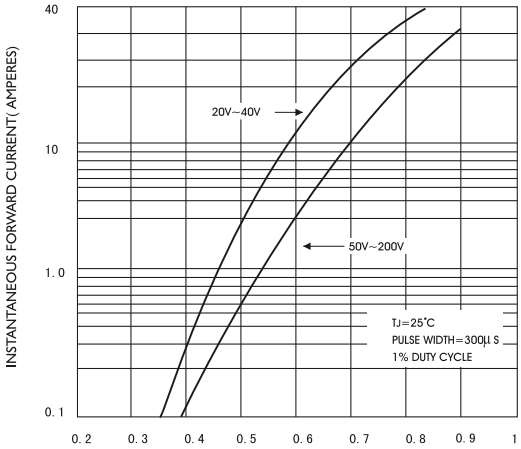


FIG.4-TYPICAL JUNCTION CAPACITANCE

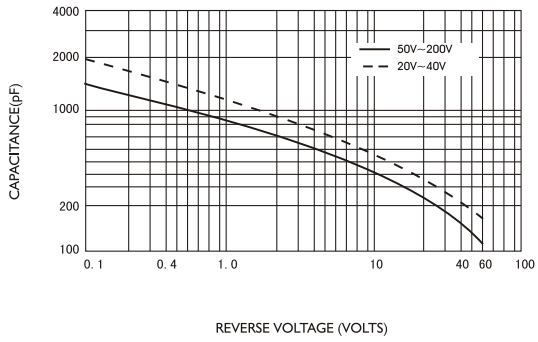


FIG.3-TYPICAL REVERSE CHARACTERISTICS

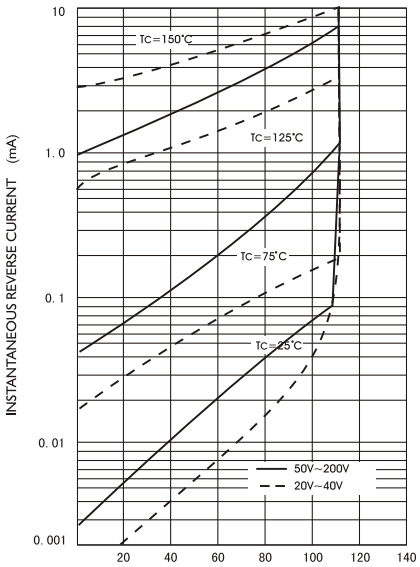


FIG.5-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

